



Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_{D@TC=25}$	26	A
	$I_{D@TC=75}$	20	A
	$I_{D@TC=100}$	16	A
Pulsed Drain Current	$I_{DM}$	78	A
Total Power Dissipation	$P_D@TC=25$	4.0	W
Total Power Dissipation	$P_D@TA=25$	0.75	W
Operating Junction Temperature	$T_J$	-55 to 150	
Storage Temperature	$T_{STG}$	-55 to 150	
Single Pulse Avalanche Energy	$E_{AS}$	320	mJ

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	32	$^{\circ}C/W$
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	170	$^{\circ}C/W$
Soldering temperature, wave soldering for 10s	$T_{sold}$	-	-	265	$^{\circ}C$

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance		$V_{GS}=10V, I_D=15A$				
		$V_{GS}=4.5V, I_D=12A$				
Forward Transconductance	$g_{FS}$	$V_{DS}=25V, I_D=10A$				
Source-drain voltage	$V_{SD}$	$I_S=15A$				

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	$C_{iss}$	$f = 1MHz,$ $V_{DS}=25V$	-	5200	-	pF
Output capacitance	$C_{oss}$		-	650	-	
Reverse transfer capacitance	$C_{rss}$		-	500	-	

**Gate Charge characteristics( $T_a=25$  )**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Gate Resistance	$R_g$	$f = 1MHz$		1.0		
Total gate charge	$Q_g$	$V_{DD} = 25V$ $I_D = 8A$ $V_{GS} = 10V$	-	104	-	nC
Gate - Source charge	$Q_{gs}$		-	14	-	
Gate - Drain charge	$Q_{gd}$		-	31	-	
Turn-ON Delay time	$t_{D(on)}$			12		ns
Turn-ON Rise time				7		ns

Turn-Off Delay time				53		ns
Turn-Off Fall time				14		ns
				19.3		ns
				10.9		ns
				8.4		ns
				9.5		ns

Note:

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Fig.1 Power Dissipation

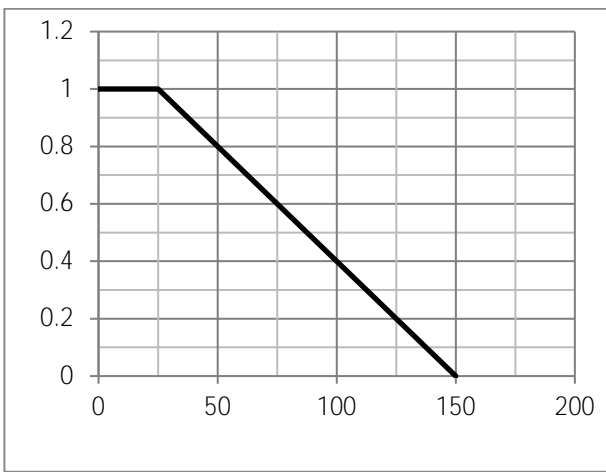


Fig.2 Typical output Characteristics

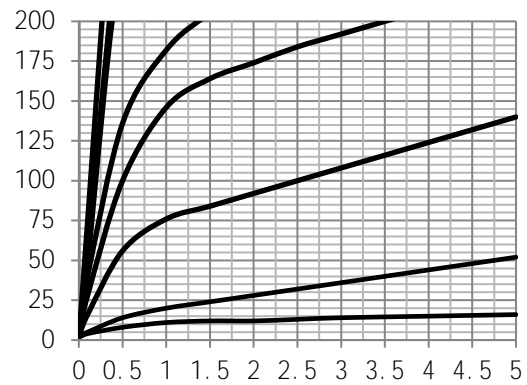


Fig.3 Threshold Voltage V.S Junction Temperature

Fig.4 Resistance V.S Drain Current



Fig.7 Safe Operating Area

Fig.8 Drain Current

Fig.9

Fig.10

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Fig.17 Avalanche Measurement Circuit

Fig.18 Avalanche Waveform



(SOP8)

Unit mm

SYMBOL	mi n	TYP	max	SYMBOL	mi n		max
A	4.80		5.00	C	1.30		1.50
A1	0.37		0.47	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.19	0.20	0.23
B1	3.80		4.00	D		1.05	
B2							